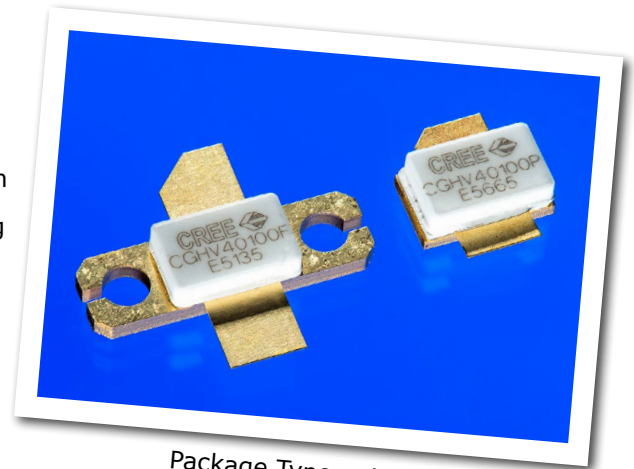


# CGHV40100

**100 W, DC - 4.0 GHz, 50 V, GaN HEMT**

Cree's CGHV40100 is an unmatched, gallium nitride (GaN) high electron mobility transistor (HEMT). The CGHV40100, operating from a 50 volt rail, offers a general purpose, broadband solution to a variety of RF and microwave applications. GaN HEMTs offer high efficiency, high gain and wide bandwidth capabilities making the CGHV40100 ideal for linear and compressed amplifier circuits. The transistor is available in a 2-lead flange and pill package.



Package Types: 440193 & 440206  
PN: CGHV40100F & CGHV40100P

## Typical Performance Over 500 MHz - 2.5 GHz ( $\tau_c = 25^\circ\text{C}$ ), 50 V

Parameter	500 MHz	1.0 GHz	1.5 GHz	2.0 GHz	2.5 GHz	Units
Small Signal Gain	17.6	16.9	17.7	17.5	14.8	dB
Saturated Output Power	147	100	141	116	112	W
Drain Efficiency @ $P_{SAT}$	68	56	58	54	54	%
Input Return Loss	6	5.1	10.5	5.5	8.8	dB

Note:  
Measured CW in the CGHV40100F-TB application circuit.

## Features

- Up to 4 GHz Operation
- 100 W Typical Output Power
- 17.5 dB Small Signal Gain at 2.0 GHz
- Application Circuit for 0.5 - 2.5 GHz
- 55 % Efficiency at  $P_{SAT}$
- 50 V Operation



Large Signal Models Available for SiC & GaN



## Absolute Maximum Ratings (not simultaneous) at 25 °C Case Temperature

Parameter	Symbol	Rating	Units	Conditions
Drain-Source Voltage	$V_{DSS}$	125	Volts	25 °C
Gate-to-Source Voltage	$V_{GS}$	-10, +2	Volts	25 °C
Storage Temperature	$T_{STG}$	-65, +150	°C	
Operating Junction Temperature	$T_J$	225	°C	
Maximum Forward Gate Current	$I_{GMAX}$	20.8	mA	25 °C
Maximum Drain Current <sup>1</sup>	$I_{DMAX}$	8.7	A	25 °C
Soldering Temperature <sup>2</sup>	$T_S$	245	°C	
Screw Torque	$\tau$	40	in-oz	
Thermal Resistance, Junction to Case <sup>3</sup>	$R_{\theta JC}$	1.62	°C/W	85 °C
Thermal Resistance, Junction to Case <sup>4</sup>	$R_{\theta JC}$	1.72	°C/W	85 °C
Case Operating Temperature <sup>5</sup>	$T_C$	-40, +150	°C	30 seconds

Note:

<sup>1</sup> Current limit for long term, reliable operation

<sup>2</sup> Refer to the Application Note on soldering at [www.cree.com/products/wireless\\_appnotes.asp](http://www.cree.com/products/wireless_appnotes.asp)

<sup>3</sup> Measured for the CGHV40100P at  $P_{DISS} = 83$  W.

<sup>4</sup> Measured for the CGHV40100F at  $P_{DISS} = 83$  W.

<sup>5</sup> See also, Power Derating Curve on Page 7

## Electrical Characteristics ( $T_C = 25^\circ\text{C}$ )

Characteristics	Symbol	Min.	Typ.	Max.	Units	Conditions
<b>DC Characteristics<sup>1</sup></b>						
Gate Threshold Voltage	$V_{GS(th)}$	-3.8	-3.0	-2.3	$V_{DC}$	$V_{DS} = 10$ V, $I_D = 20.8$ mA
Gate Quiescent Voltage	$V_{GS(Q)}$	-	-2.7	-	$V_{DC}$	$V_{DS} = 50$ V, $I_D = 0.6$ A
Saturated Drain Current <sup>2</sup>	$I_{DS}$	15.6	18.7	-	A	$V_{DS} = 6.0$ V, $V_{GS} = 2.0$ V
Drain-Source Breakdown Voltage	$V_{BR}$	150	-	-	$V_{DC}$	$V_{GS} = -8$ V, $I_D = 20.8$ mA
<b>RF Characteristics<sup>3</sup> (<math>T_C = 25^\circ\text{C}</math>, <math>F_0 = 2.0</math> GHz unless otherwise noted)</b>						
Small Signal Gain	$G_{SS}$	-	17.5	-	dB	$V_{DD} = 50$ V, $I_{DQ} = 0.6$ A
Power Gain	$G_P$	-	11.0	-	dB	$V_{DD} = 50$ V, $I_{DQ} = 0.6$ A, $P_{OUT} = P_{SAT}$
Power Output at Saturation <sup>4</sup>	$P_{SAT}$	-	116	-	W	$V_{DD} = 50$ V, $I_{DQ} = 0.6$ A
Drain Efficiency	$\eta$	-	54	-	%	$V_{DD} = 50$ V, $I_{DQ} = 0.6$ A, $P_{OUT} = P_{SAT}$
Output Mismatch Stress	VSWR	-	-	10 : 1	$\Psi$	No damage at all phase angles, $V_{DD} = 50$ V, $I_{DQ} = 0.6$ A, $P_{OUT} = 100$ W CW
<b>Dynamic Characteristics<sup>5</sup></b>						
Input Capacitance	$C_{GS}$	-	29.3	-	pF	$V_{DS} = 50$ V, $V_{GS} = -8$ V, $f = 1$ MHz
Output Capacitance	$C_{DS}$	-	7.3	-	pF	$V_{DS} = 50$ V, $V_{GS} = -8$ V, $f = 1$ MHz
Feedback Capacitance	$C_{GD}$	-	0.61	-	pF	$V_{DS} = 50$ V, $V_{GS} = -8$ V, $f = 1$ MHz

Notes:

<sup>1</sup> Measured on wafer prior to packaging.

<sup>2</sup> Scaled from PCM data.

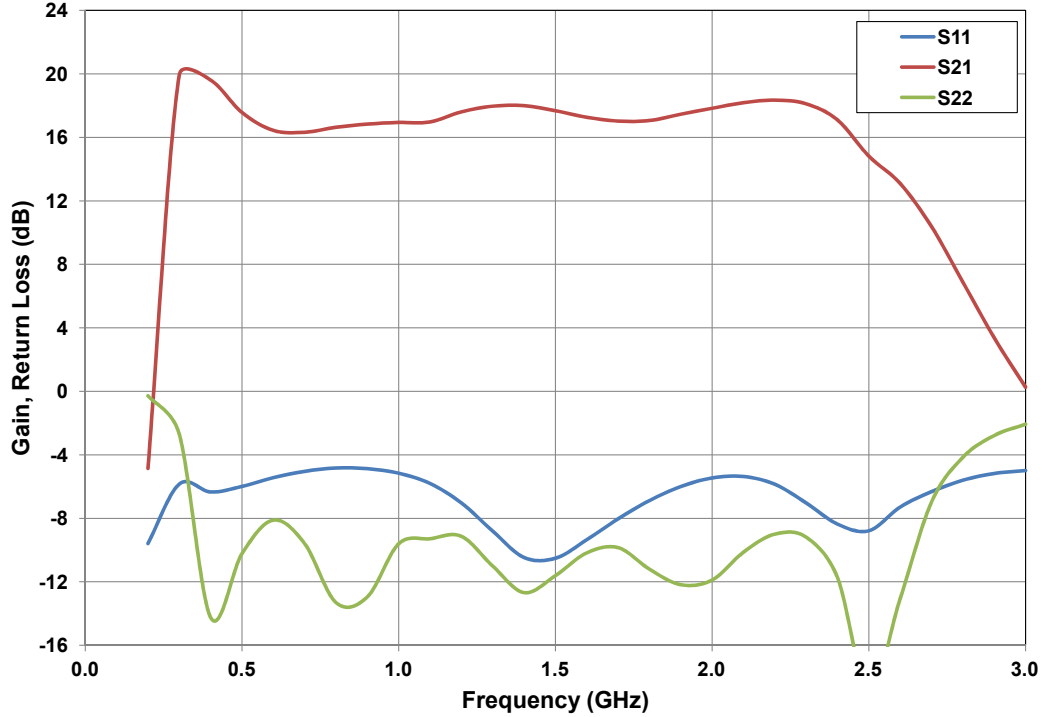
<sup>3</sup> Measured in CGHV40100-TB.

<sup>4</sup>  $P_{SAT}$  is defined as  $I_G$

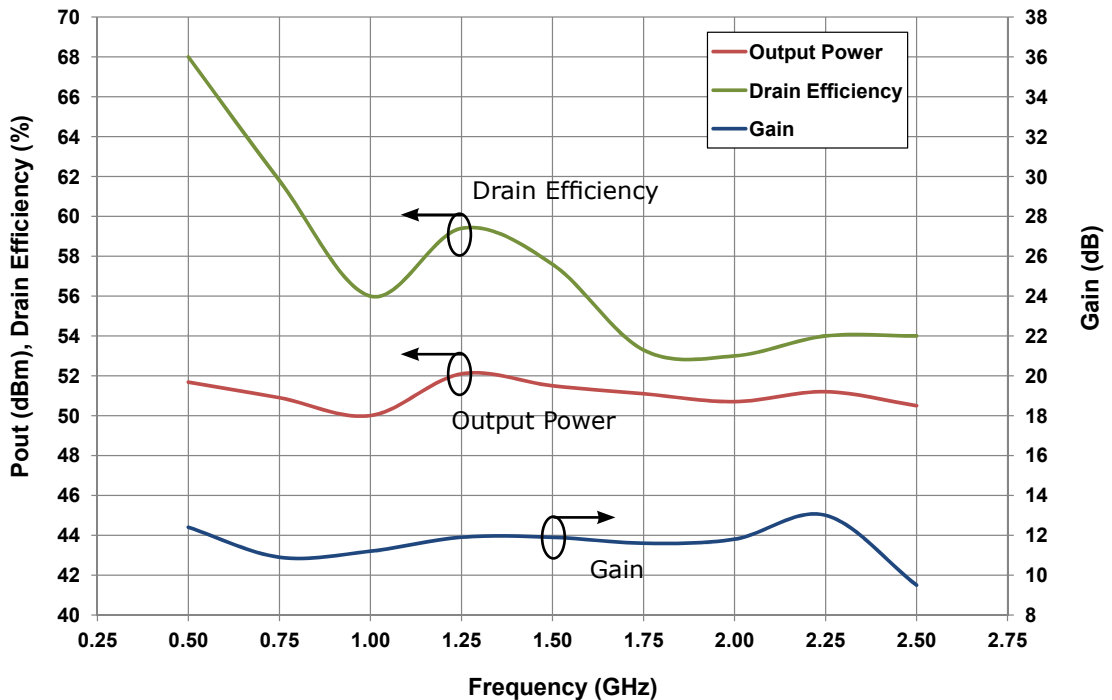
<sup>5</sup> Includes package

## CGHV40100 Typical Performance

**Figure 1. - Small Signal Gain and Return Losses versus Frequency of the CGHV40100 in the application circuit CGHV40100-TB**  
 $V_{DD} = 50\text{ V}$ ,  $I_{DQ} = 600\text{ mA}$ ,  $T_{case} = 25^\circ\text{C}$



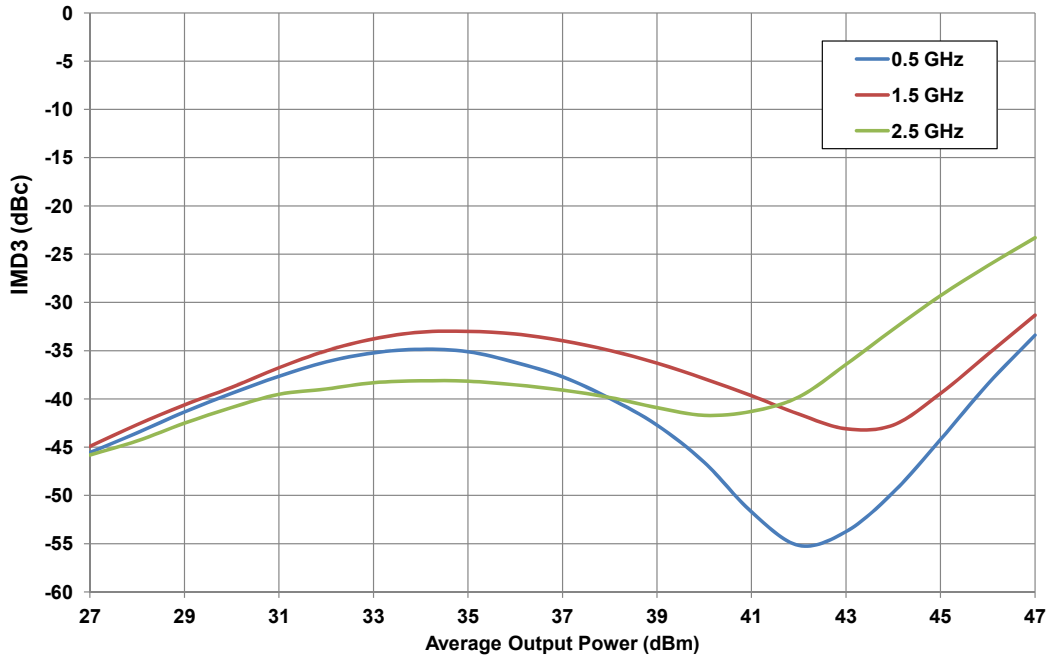
**Figure 2. - Output Power and Drain Efficiency vs Frequency**  
 $V_{DD} = 50\text{ V}$ ,  $I_{DQ} = 600\text{ mA}$



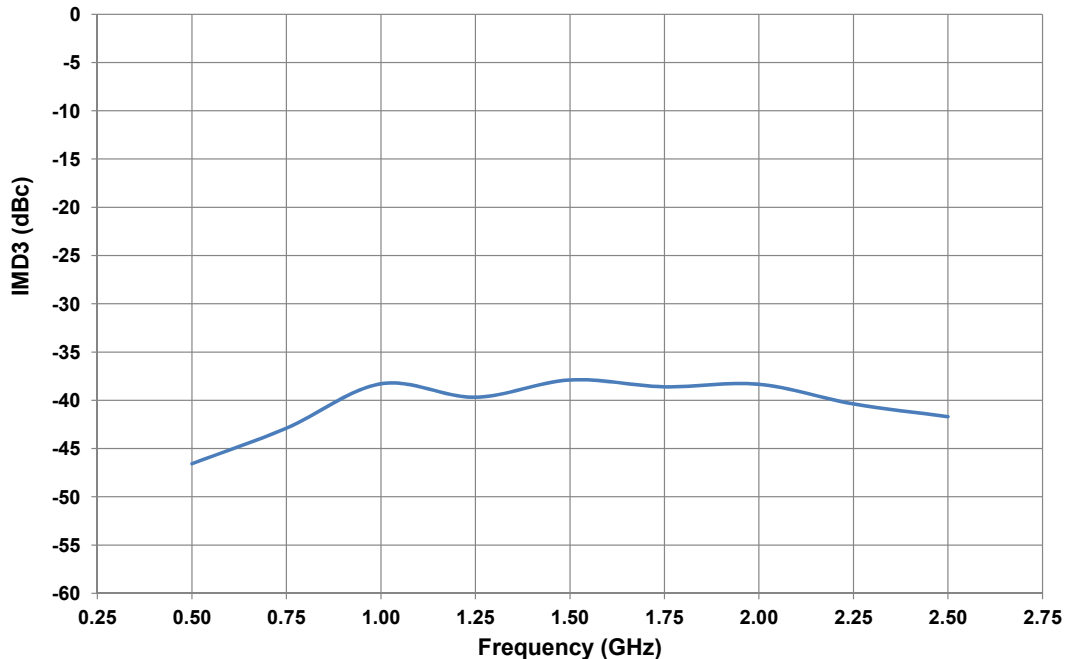


## CGHV40100 Typical Performance

**Figure 3. - Third Order Intermodulation Distortion vs Average Output Power of CGHV40100 measured in Broadband Amplifier Circuit CGHV40100-TB**  
Spacing = 1 MHz,  $V_{DD} = 50\text{ V}$ ,  $I_{DQ} = 600\text{ mA}$ ,  $T_{case} = 25^\circ\text{C}$



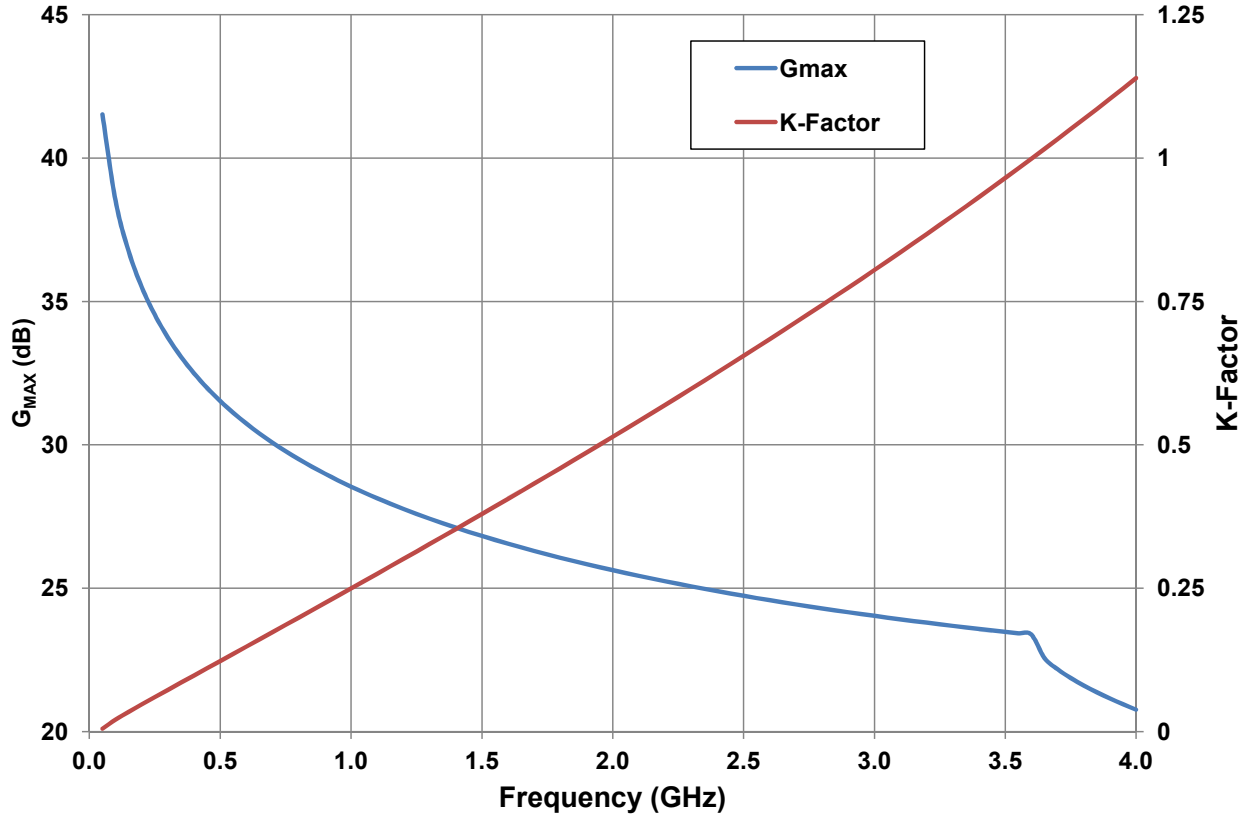
**Figure 4. - Third Order Intermodulation Distortion vs Frequency of CGHV40100 measured in Broadband Amplifier Circuit CGHV40100-TB**  
Spacing = 1 MHz,  $V_{DD} = 50\text{ V}$ ,  $I_{DQ} = 600\text{ mA}$ ,  $T_{case} = 25^\circ\text{C}$



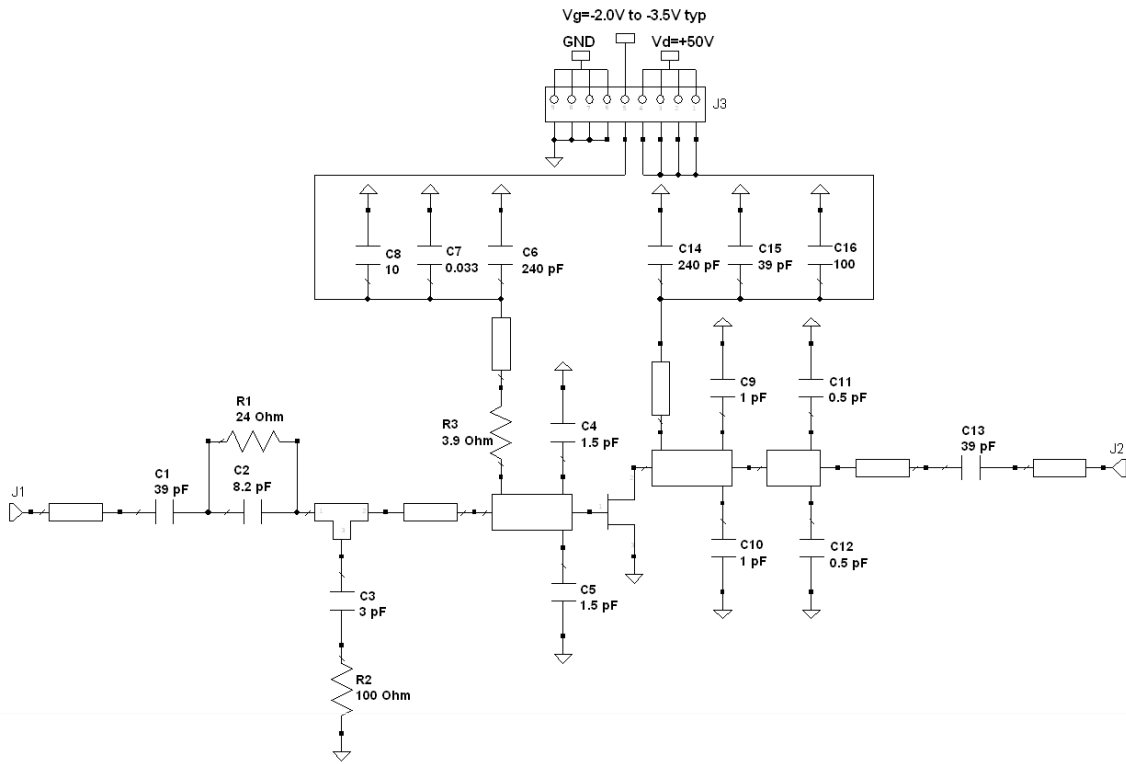


## CGHV40100 Typical Performance

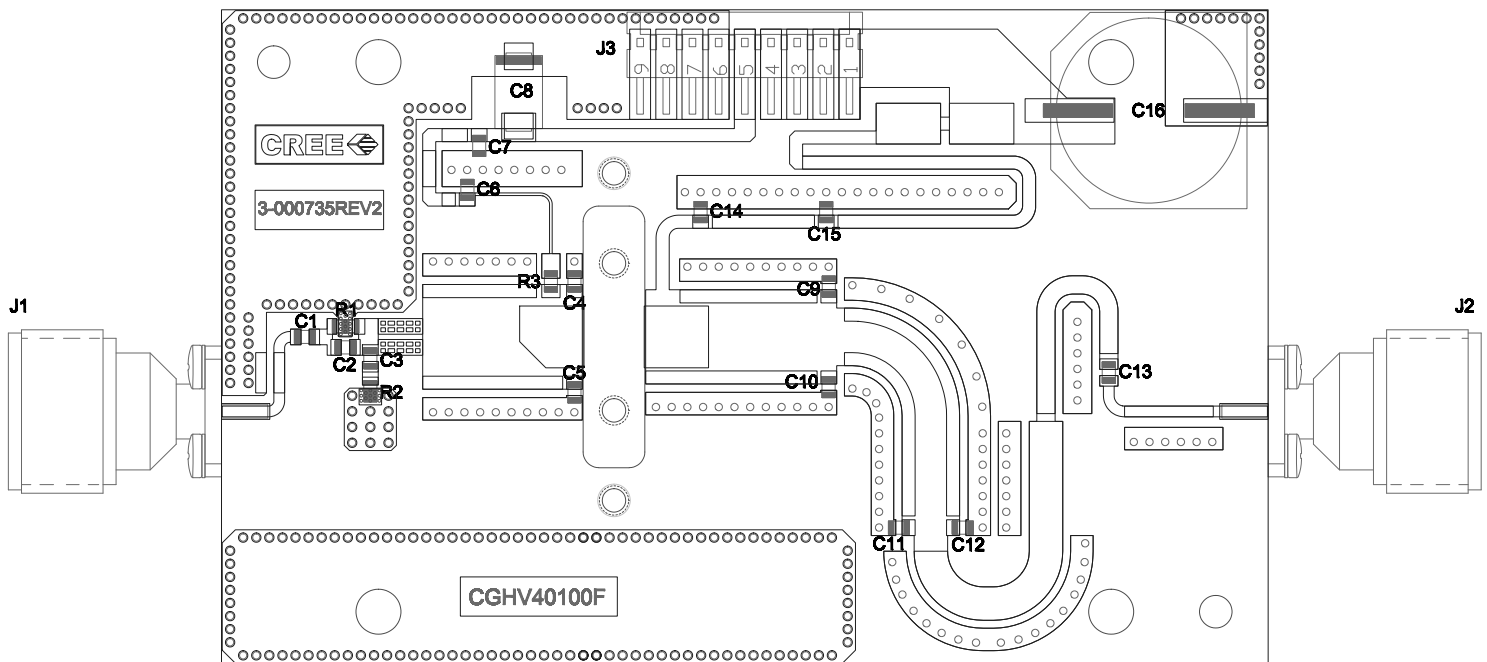
Figure 5. -  $G_{MAX}$  and K-Factor vs Frequency  
 $V_{DD} = 50\text{ V}$ ,  $I_{DQ} = 600\text{ mA}$ ,  $T_{case} = 25^\circ\text{C}$



# CGHV40100-TB Application Circuit Schematic



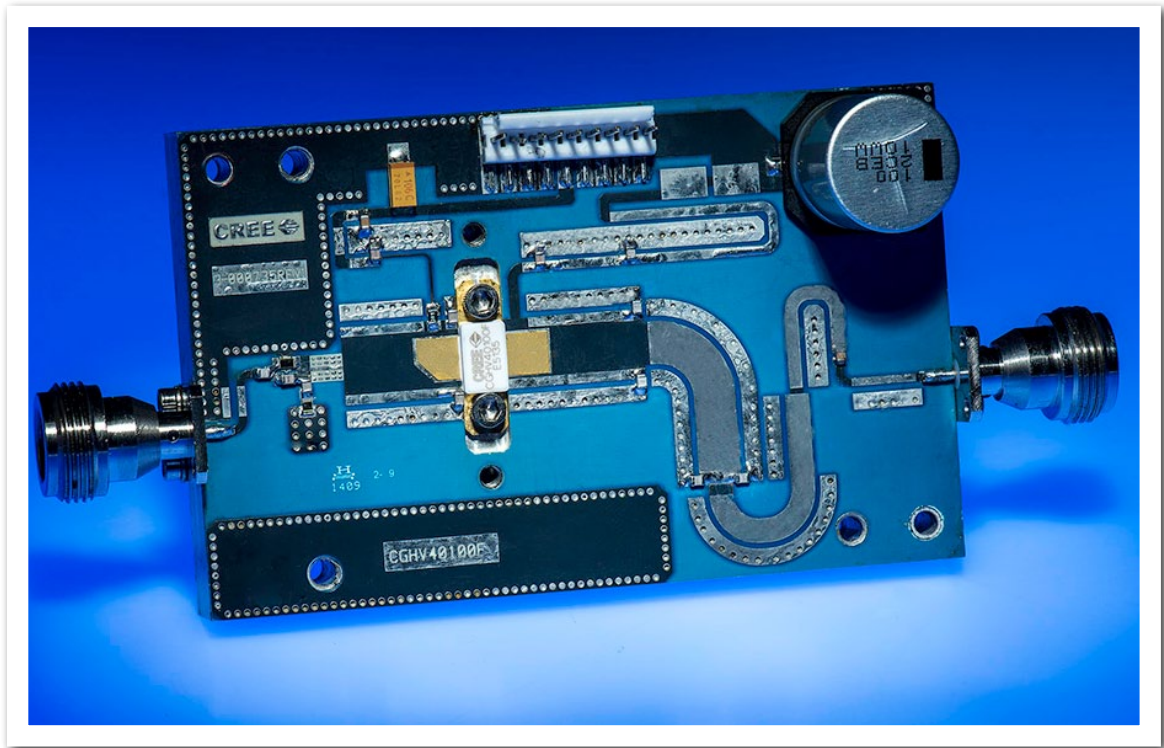
# CGHV40100-TB Application Circuit



## CGHV40100-TB Application Circuit Bill of Materials

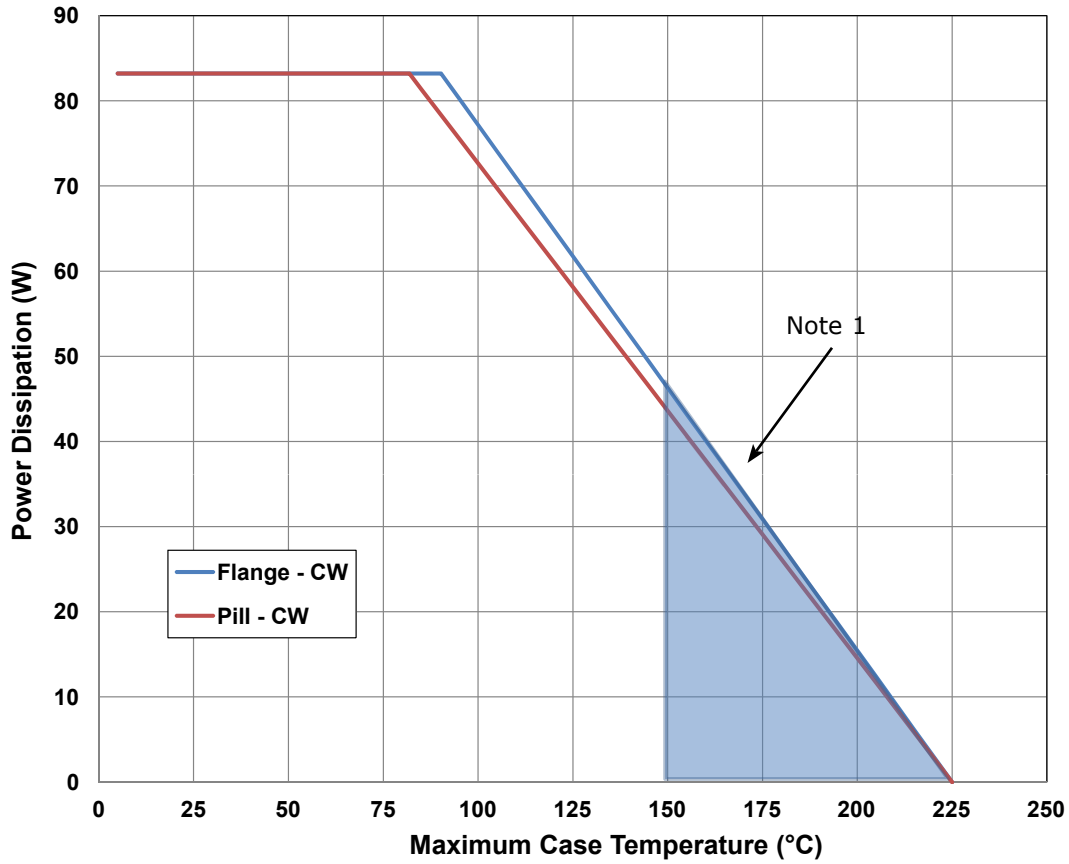
Designator	Description	Qty
C1, C13, C15	CAP, 39 pF, $\pm 0.1$ pF, 250V, 0805, ATC600F	3
C2	CAP, 8.2 pF, $\pm 0.1$ pF, 250 V, 0806, ATC600F	1
C3	CAP, 3 pF $\pm 0.1$ pF, 250 V, 0805, ATC600F	1
C4, C5	CAP, 1.5 pF, $\pm 0.1$ pF, 250 V, 0805, ATC600F	2
C7	CAP, 33000 pF, 0805 100V, X7R	1
C6, C14	CAP, 240 pF, $\pm 0.5$ pF, 250 V, 0805, ATC600F	2
C8	CAP, 10 UF, 16V TANTALUM, 2312	1
C9, C10	CAP, 1 pF, $\pm 0.1$ pF, 250 V, 0805, ATC600F	2
C11, C12	CAP, 0.5 pF, $\pm 0.1$ pF, 250 V, 0805, ATC600F	2
C16	CAP, 100 UF, 20%, 160 V, ELEC	1
R1	RES, 24 OHMS, IMS ND3-1005CS24R0G	1
R2	RED, 100 OHMS, IMS ND3-0805EW1000G	1
R3	RES, 3.9 OHMS, 0805	1
J1, J2	CONN, N, FEM, W/.500 SMA FLNG	2
J3	HEADER RT>PLZ .1CEN LK 9POS	1
	BASEPLATE, CGH35120	1
	PCB, RO4350B, 2.5" X 4" X 0.020", CGHV40100F	1

## CGHV40100-TB Demonstration Amplifier Circuit



# CGHV40100 Power Dissipation De-rating Curve

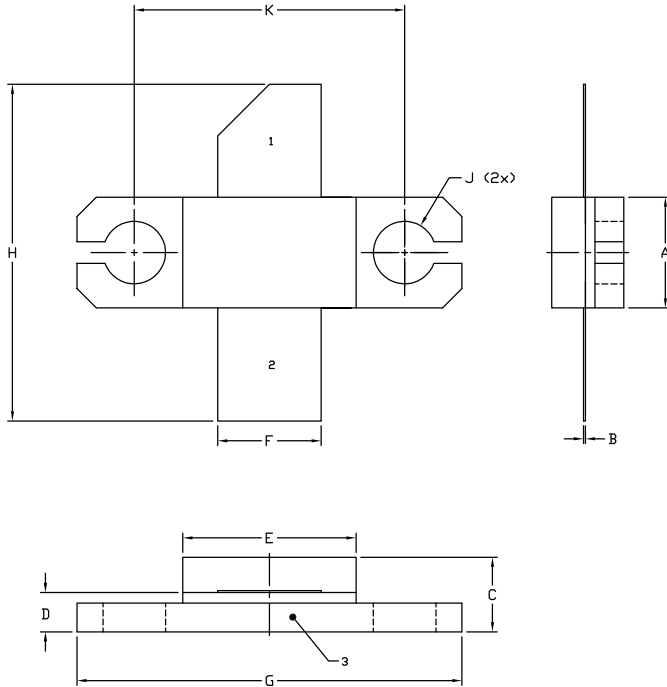
Figure 5. - Transient Power Dissipation De-Rating Curve



Note 1. Area exceeds Maximum Case Temperature (See Page 2).



## Product Dimensions CGHV40100F (Package Type — 440193)

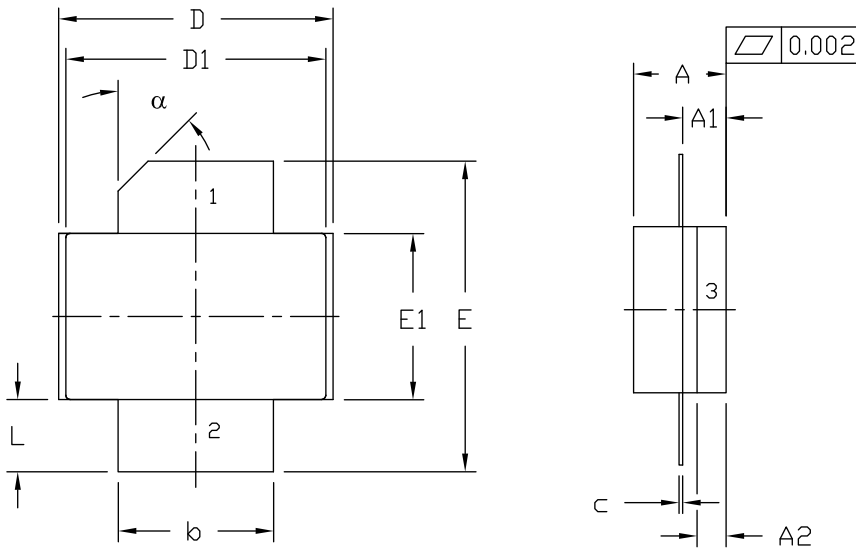


- NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
  2. CONTROLLING DIMENSION: INCH.
  3. ADHESIVE FROM LID MAY EXTEND A MAXIMUM OF 0.020" BEYOND EDGE OF LID.
  4. LID MAY BE MISALIGNED TO THE BODY OF THE PACKAGE BY A MAXIMUM OF 0.008" IN ANY DIRECTION.
  5. ALL PLATED SURFACES ARE Ni/AU.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.225	0.235	5.72	5.97
B	0.004	0.006	0.10	0.15
C	0.145	0.165	3.68	4.19
D	0.077	0.087	1.96	2.21
E	0.355	0.365	9.02	9.27
F	0.210	0.220	5.33	5.59
G	0.795	0.805	20.19	20.45
H	0.670	0.730	17.02	18.54
J	∅ .130		3.30	
k	0.562		14.28	

- PIN 1. GATE  
 PIN 2. DRAIN  
 PIN 3. SOURCE

## Product Dimensions CGHV40100P (Package Type — 440206)



- NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M - 1994.
  2. CONTROLLING DIMENSION: INCH.
  3. ADHESIVE FROM LID MAY EXTEND A MAXIMUM OF 0.020" BEYOND EDGE OF LID.
  4. LID MAY BE MISALIGNED TO THE BODY OF PACKAGE BY A MAXIMUM OF 0.008" IN ANY DIRECTION.

DIM	INCHES		MILLIMETERS		NOTES
	MIN	MAX	MIN	MAX	
A	0.125	0.145	3.18	3.68	
A1	0.057	0.067	1.45	1.70	
A2	0.035	0.045	0.89	1.14	
b	0.210	0.220	5.33	5.59	2x
c	0.004	0.006	0.10	0.15	2x
D	0.375	0.385	9.53	9.78	
D1	0.355	0.365	9.02	9.27	
E	0.400	0.460	10.16	11.68	
E1	0.225	0.235	5.72	5.97	
L	0.085	0.115	2.16	2.92	2x
α	45° REF		45° REF		

- PIN 1. GATE  
 PIN 2. DRAIN  
 PIN 3. SOURCE



## Disclaimer

Specifications are subject to change without notice. Cree, Inc. believes the information contained within this data sheet to be accurate and reliable. However, no responsibility is assumed by Cree for any infringement of patents or other rights of third parties which may result from its use. No license is granted by implication or otherwise under any patent or patent rights of Cree. Cree makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose. "Typical" parameters are the average values expected by Cree in large quantities and are provided for information purposes only. These values can and do vary in different applications and actual performance can vary over time. All operating parameters should be validated by customer's technical experts for each application. Cree products are not designed, intended or authorized for use as components in applications intended for surgical implant into the body or to support or sustain life, in applications in which the failure of the Cree product could result in personal injury or death or in applications for planning, construction, maintenance or direct operation of a nuclear facility.

For more information, please contact:

Cree, Inc.  
4600 Silicon Drive  
Durham, North Carolina, USA 27703  
[www.cree.com/wireless](http://www.cree.com/wireless)

Sarah Miller  
Marketing & Export  
Cree, RF Components  
1.919.407.5302

Ryan Baker  
Marketing  
Cree, RF Components  
1.919.407.7816

Tom Dekker  
Sales Director  
Cree, RF Components  
1.919.407.5639

# Mouser Electronics

Authorized Distributor

Click to View Pricing, Inventory, Delivery & Lifecycle Information:

[Cree, Inc.:](#)

[CGHV40100F](#) [CGHV40100F-TB](#)